

16A, 50V - 600V High Efficient Rectifier

FEATURES

TAIWAN

• AEC-Q101 qualified available

EMICONDUCTOR

- Glass passivated chip junction
- High efficiency, Low V_F
- High current capability
- High reliability
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

MECHANICAL DATA

- Case: ITO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N⋅m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I _F	16	А
V _{RRM}	50 - 600	V
I _{FSM}	250	А
T _{J MAX}	150	°C
Package	ITO-220AC	
Configuration	Single die	





PIN 1 O-

PIN 2 O-

ABSOLUTE MAXIMUM RATII		HERAF	HERAF	r	HERAF	HERAF	HERAF	
PARAMETER	SYMBOL	1601G	1602G	1603G	1604G	1605G	1606G	UNIT
Marking code on the device		HERAF 1601G	HERAF 1602G	HERAF 1603G	HERAF 1604G	HERAF 1605G	HERAF 1606G	
Repetitive peak reverse voltage	V _{RRM}	50	100	200	300	400	600	V
Reverse voltage, total rms value	V _{R(RMS)}	35	70	140	210	280	420	V
Forward current	I _F			1	6			А
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I _{FSM}	250		A				
Junction temperature	TJ	-55 to +150		°C				
Storage temperature	T _{STG}	-55 to +150		°C				



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case resistance	R _{eJC}	2	°C/W

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage ⁽¹⁾	HERAF1601G HERAF1602G HERAF1603G HERAF1604G	I _F = 16A, T _J = 25°C	V _F	-	1.0	V
	HERAF1605G			-	1.3	V
	HERAF1606G			-	1.7	V
Reverse current @ rated V _R ⁽²⁾		$T_J = 25^{\circ}C$	- I _R	-	10	μA
		T _J = 125°C		-	400	μA
Junction capacitance	HERAF1601G HERAF1602G HERAF1603G HERAF1604G HERAF1605G	1MHz, V _R = 4.0V	CJ	150	-	pF
	HERAF1606G			110	-	pF
Reverse recovery time	HERAF1601G HERAF1602G HERAF1603G HERAF1604G HERAF1605G	IF = 0.5A, IR = 1.0A Irr = 0.25A	t _{rr}	-	50	ns
	HERAF1606G			-	80	ns

Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING
HERAF16xG	ITO-220AC	50 / Tube
HERAF16xGH	ITO-220AC	50 / Tube

Notes:

1. "x" defines voltage from 50V(HERAF1601G) to 600V(HERAF1606G)

2. "H" means AEC-Q101 qualified



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CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

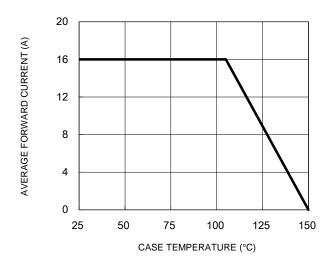


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics

100 1000 INSTANTANEOUS REVERSE CURRENT (µA) INSTANTANEOUS FORWARD CURRENT (A) HERAF1601G -1604G T_{.1}=125°C 100 10 HERAF1605G 10 1 HERAF1606G T_=25°C Pulse width 300µs 1% duty cycle 1 0.1 20 10 30 40 50 60 70 80 90 100 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 PERCENT OF RATED PEAK REVERSE VOLTAGE (%)

1000

100

10

CAPACITANCE (pF)

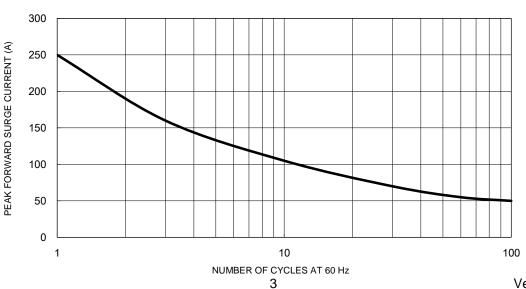


Fig.5 Maximum Non-Repetitive Forward Surge Current

f=1.0MHz Vsig=50mVp-p 1 10 100 1 REVERSE VOLTAGE (V)

HERAF1606G

Fig.4 Typical Forward Characteristics

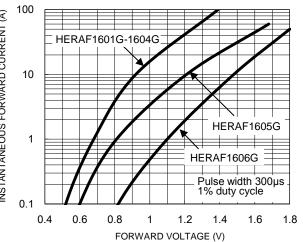


Fig.2 Typical Junction Capacitance

HERAF1601G-1005G



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CHARACTERISTICS CURVES

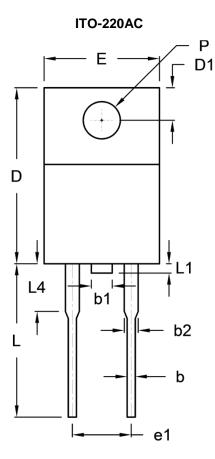
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

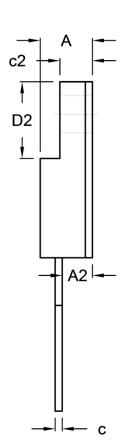
50Ω 10Ω - trr 🗕 NONINDUCTIVE NONINDUCTIVE ~~~ ~~~ +0.5A (-) ± DUT • (+) 50Vdc PULSE 0 GENERATOR = (approx) -0.25A (NOTE 2) (-) IΩ OSCILLOSCOPE 6 (+) (NOTE 1) -1.0A NOTES: 1. Rise Time=7ns max. Input Impedance= ≐ 1 megohm 22pf 2. Rise Time=10ns max. Sourse Impedance= 50 ohms

Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram

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PACKAGE OUTLINE DIMENSIONS





DIM.	Unit (mm)		Unit ((inch)	
Divi.	Min.	Max.	Min.	Max.	
A	4.30	4.70	0.169	0.185	
A2	2.30	2.90	0.091	0.114	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
с	0.46	0.76	0.018	0.030	
c2	2.50	3.10	0.098	0.114	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
E	9.60	10.30	0.378	0.406	
e1	4.95	5.20	0.195	0.205	
L	12.60	13.80	0.496	0.543	
L1	0.00	1.60	0.000	0.063	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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